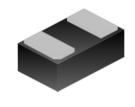


Bi-directional 18V Low Capacitance ESD Protector

Description

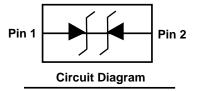
The PESDMC2FD18VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

Feature

- \rightarrow 30W peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns</p>
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±15KV(air), ±15KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)



Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

18B

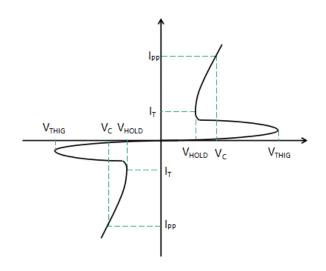
Marking (Top View)

Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating

Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I⊤		
lτ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
lF	Forward Current		
VF	Forward Voltage @ I _F		



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				18	V
Breakdown Voltage	V_{BR}	I _t =1mA	19		23	V
Reverse holding voltage	VHOLD	I _{HOLD} =60mA	2.0	2.8	3.5	V
Reverse Leakage Current	I _R	V _{RWM} =18V T=25°C			1.0	μA
Clamping Voltage	Vc	TLP=16A or ESD=8KV		9		٧
Clamping Voltage	Vc	I _{PP} =1A			6	V
Clamping Voltage	Vc	I _{PP} =4A			8	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		0.4	0.5	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20μs)	P _{pp}	30	W
Peak Pulse Current(t _p =8/20μs)	I _{pp}	4	A
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

Typical Characteristics

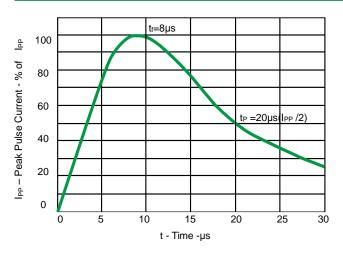


Fig 1.Pulse Waveform

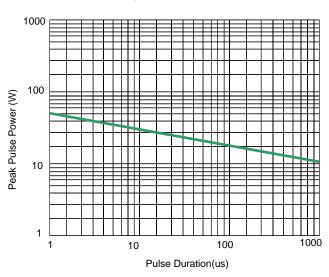


Fig 3. Non-Repetitive Peak Pulse Power vs. Pulse time

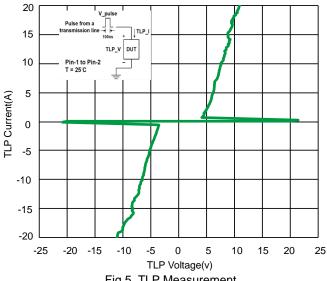


Fig 5. TLP Measurement

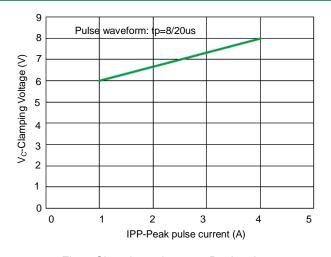


Fig 2. Clamping voltage vs. Peak pulse current

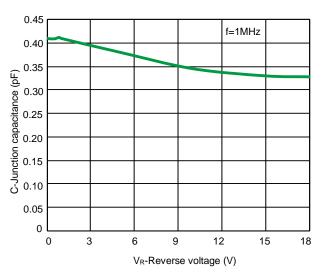


Fig 4. Capacitance vs. Reveres voltage

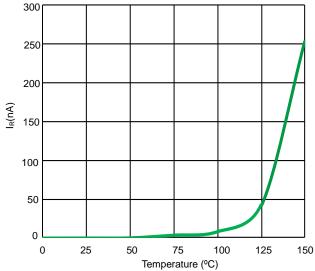
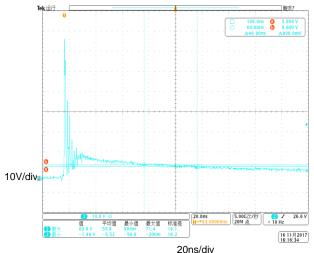


Fig 6. Typical Leakage Current vs. Temperature



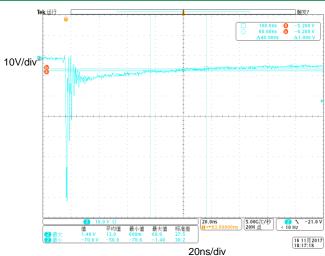
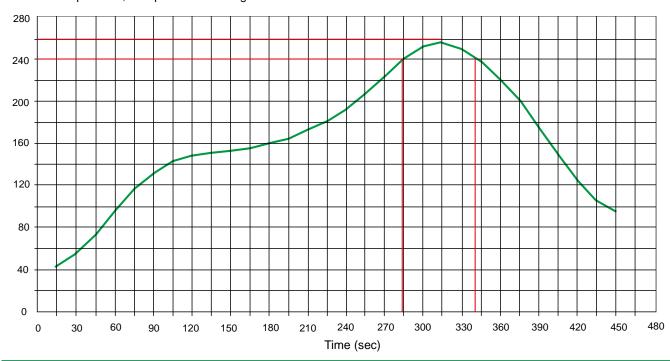


Fig 7. ESD clamping voltage (IEC61000-4-2 +8KV contact)

Fig 8. ESD clamping voltage (IEC61000-4-2-8KV contact)

Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

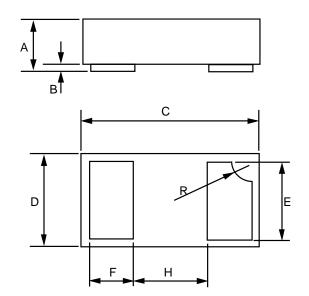


PCB Design

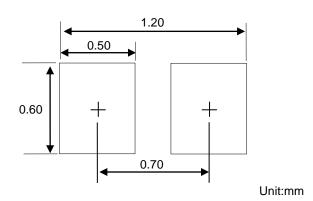
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1006-2L)



Dim	Inc	hes	Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.013	0.020	0.34	0.50	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
Е	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Тур.		0.40Тур.		
R	0.001	0.005	0.05	0.15	



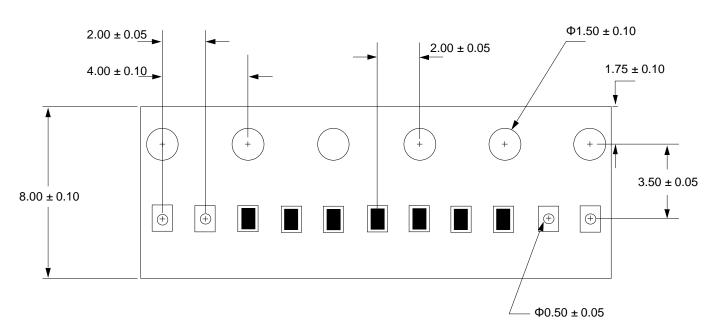
Suggested PCB Layout

Ordering information

Device	Package	Reel	Shipping
PESDMC2FD18VB	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

Load with information





Unit: mm

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